

Abstract of the Disclosure:

A light-emitting device is based on a gallium nitride-based compound semiconductor. A light-emitting layer with a first and a second main surface is formed from a compound 5 semiconductor based on gallium nitride. A first coating layer, which is joined to the first main surface of the light-emitting layer, is formed from an n-type compound semiconductor based on gallium nitride. The composition of which differs from that of the compound semiconductor of the 10 light-emitting layer. A second coating layer, which is joined to the second main surface of the light-emitting layer, is formed from a p-type compound semiconductor based on gallium nitride, the composition of which differs from that of the compound semiconductor of the light-emitting layer. To 15 improve the light yield of the device, the thickness of the light-emitting layer in the vicinity of dislocations is configured to be lower than in the remaining regions.

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